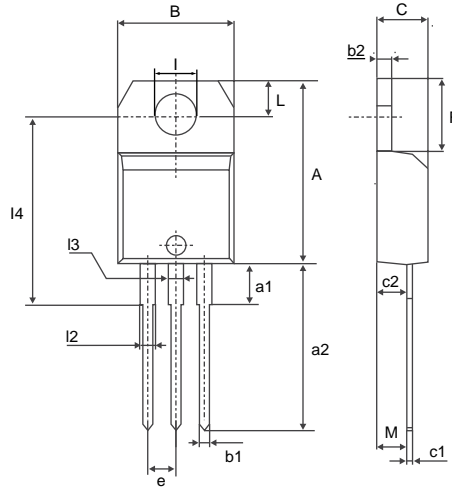
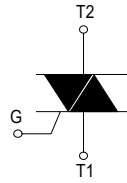


# BTA16

## Discrete Triacs(Isolated)



Ref.	Dimensions		
	Millimeters		
	Min.	Typ.	Max.
A	15.20		15.90
a1		3.75	
a2	13.00		14.00
B	10.00		10.40
b1	0.61		0.88
b2	1.23		1.32
C	4.40		4.60
c1	0.49		0.70
c2	2.40		2.72
e	2.40		2.70
F	6.20		6.60
I	3.73		3.88
L	2.65		2.95
I2	1.14		1.70
I3	1.14		1.70
I4	15.80	16.40	16.80
M		2.6	

	$V_{DRM}/V_{RRM}$	$V_{DSM}/V_{RSM}$
	V	V
BTA16-200	200	300
BTA16-400	400	500
BTA16-600	600	700
BTA16-800	800	900
BTA16-1000	1000	1100
BTA16-1200	1200	1300

### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
$I_{T(RMS)}$	RMS on-state current (full sine wave)	TO-220AB $T_c = 100^\circ\text{C}$	16 A
$I_{TSM}$	Non repetitive surge peak on-state current (full cycle, $T_j$ initial = $25^\circ\text{C}$ )	F = 60 Hz t = 16.7 ms	160 A
		F = 50 Hz t = 20 ms	168 A
$I^2t$	$I^2t$ Value for fusing	tp = 10 ms	144 $\text{A}^2\text{s}$
dI/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$ , tr ≤ 100 ns	F = 120 Hz $T_j = 125^\circ\text{C}$	50 A/μs
$V_{DSM}/V_{RSM}$	Non repetitive surge peak off-state voltage	tp = 10 ms $T_j = 25^\circ\text{C}$	$V_{DRM}/V_{RRM} + 100$ V
$I_{GM}$	Peak gate current	tp = 20 μs $T_j = 125^\circ\text{C}$	4 A
$P_{G(AV)}$	Average gate power dissipation	$T_j = 125^\circ\text{C}$	1 W
$T_{stg}$ $T_j$	Storage junction temperature range Operating junction temperature range		- 40 to + 150 - 40 to + 125 $^\circ\text{C}$

### ELECTRICAL CHARACTERISTICS ( $T_j = 25^\circ\text{C}$ , unless otherwise specified)

#### ■ SNUBBERLESS and LOGIC LEVEL(3 Quadrants)

Symbol	Test Conditions	Quadrant		BTA			Unit
				SW	CW	BW	
$I_{GT}$	$V_D = 12\text{ V}$ $R_L = 33\ \Omega$	I - II - III	MAX.	10	35	50	mA
$V_{GT}$		I - II - III	MAX.	1.3			V
$V_{GD}$	$V_D = V_{DRM}$ $R_L = 3.3\ \text{k}\Omega$ $T_j = 125^\circ\text{C}$	I - II - III	MIN.	0.2			V
$I_H$	$I_T = 500\ \text{mA}$		MAX.	15	35	50	mA
$I_L$	$I_G = 1.2 I_{GT}$	I - III	MAX.	25	50	70	mA
		II		30	60	80	
dV/dt	$V_D = 67\% V_{DRM}$ gate open $T_j = 125^\circ\text{C}$		MIN.	400	500	1000	V/μs
(di/dt) <sub>c</sub>	Without snubber $T_j = 125^\circ\text{C}$		MIN.		8.5	14	A/ms

Viso>2500VAC 1min



# BTA16

## Discrete Triacs(Isolated)

### ■ STANDARD (4 Quadrants)

Symbol	Test Conditions	Quadrant		Value	Unit
$I_{GT}$	$V_D = 12\text{ V}$ $R_L = 33\ \Omega$	I - II - III IV	MAX.	50 100	mA
$V_{GT}$		ALL	MAX.	1.3	V
$V_{GD}$	$V_D = V_{DRM}$ $R_L = 3.3\ \Omega$ $T_j = 125^\circ\text{C}$	ALL	MIN.	0.2	V
$I_H$	$I_T = 500\text{ mA}$		MAX.	50	mA
$I_L$	$I_G = 1.2 I_{GT}$	I - III - IV	MAX.	60	mA
		II		120	
dV/dt	$V_D = 67\% V_{DRM}$ gate open $T_j = 125^\circ\text{C}$		MIN.	400	V/ $\mu\text{s}$
(dV/dt)c	(dI/dt)c = 7A/ms $T_j = 125^\circ\text{C}$		MIN.	10	V/ $\mu\text{s}$

### STATIC CHARACTERISTICS

Symbol	Test Conditions			Value	Unit
$V_{TM}$	$I_{TM} = 6\text{ A}$ $t_p = 380\ \mu\text{s}$	$T_j = 25^\circ\text{C}$	MAX.	1.55	V
$V_{TO}$	Threshold voltage	$T_j = 125^\circ\text{C}$	MAX.	0.85	V
$R_d$	Dynamic resistance	$T_j = 125^\circ\text{C}$	MAX.	60	m $\Omega$
$I_{DRM}$	$V_{DRM} = V_{RRM}$	$T_j = 25^\circ\text{C}$	MAX.	5	$\mu\text{A}$
$I_{RRM}$		$T_j = 125^\circ\text{C}$		1	mA

### THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case (AC)	1.2	$^\circ\text{C/W}$
$R_{th(j-a)}$	Junction to ambient	60	$^\circ\text{C/W}$

### PRODUCT SELECTOR

Part Number	Voltage (xxx)		Sensitivity	Type	Package
	200 V	~ 1200 V			
BTA16	X	X	10~50 mA	Standard	TO-220AB

### OTHER INFORMATION

Part Number	Marking	Weight	Base quantity	Packing mode
BTA16	BTA16	2 g	250	Bulk



# BTA16

## Discrete Triacs(Isolated)

Fig.1: Maximum power dissipation versus RMS on-state current (full cycle).

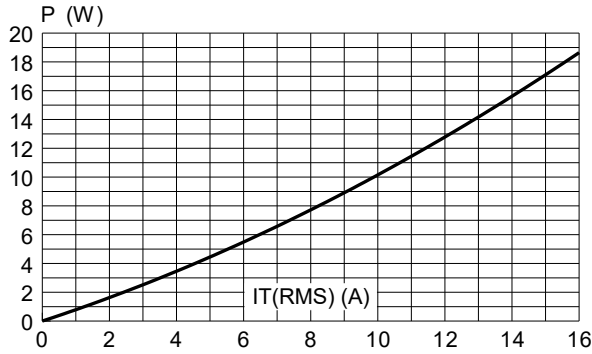


Fig.2: RMS on-state current versus case temperature (full cycle).

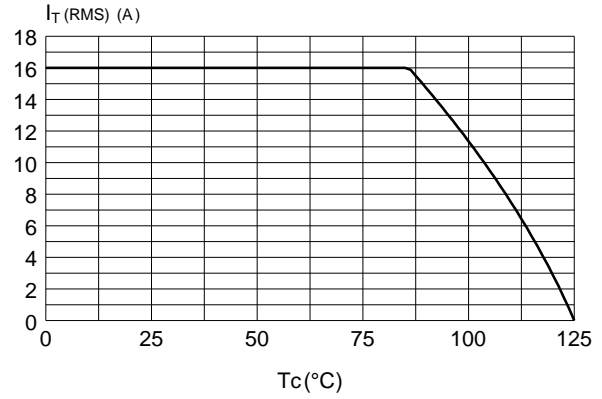


Fig.3: Relative variation of thermal impedance versus pulse duration.

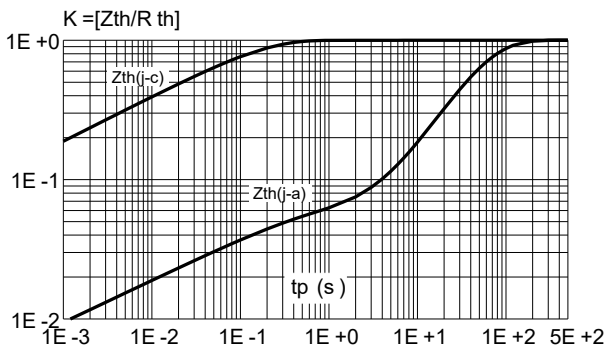


Fig.4: On-state characteristics (maximum values)

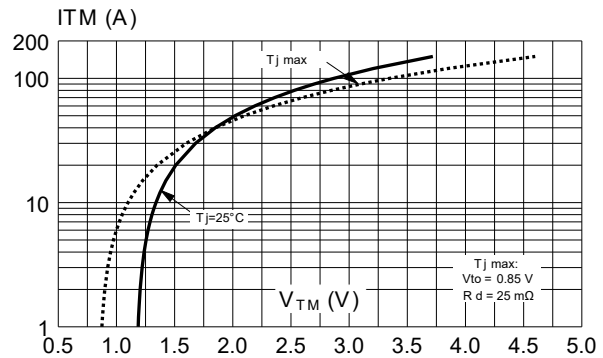
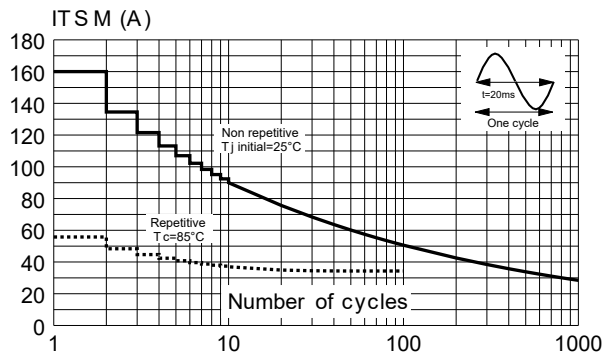


Fig.5: Surge peak on-state current versus number of cycles.



# BTA16

## Discrete Triacs(Isolated)

Fig.6: Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 10\text{ms}$ , and corresponding value of  $I^2t$ .

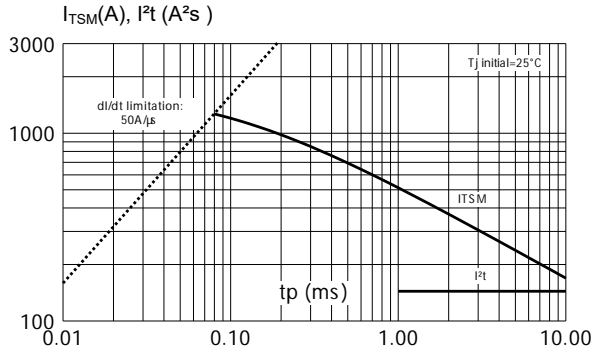


Fig.7: Relative variation of gate trigger current, holding current and latching current versus junction temperature (typical values).

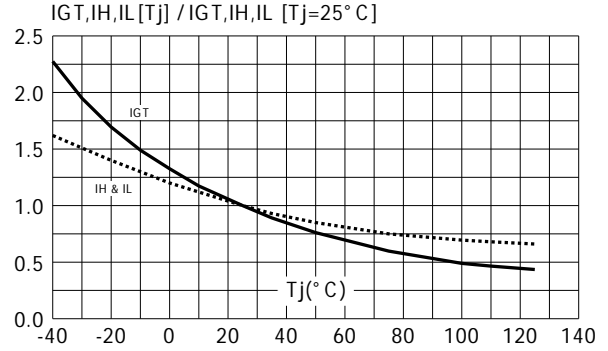


Fig.8: Relative variation of critical rate of decrease of main current versus  $(dV/dt)_c$  (typical values).

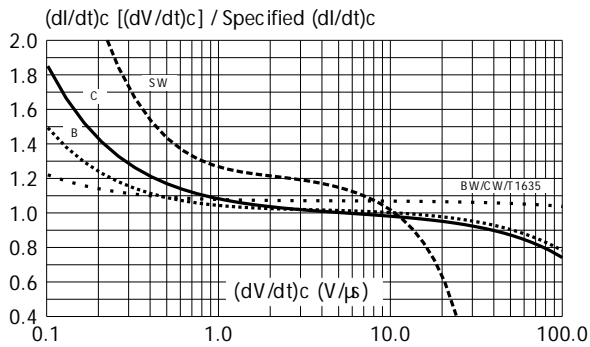


Fig.9: Relative variation of critical rate of decrease of main current versus junction temperature

